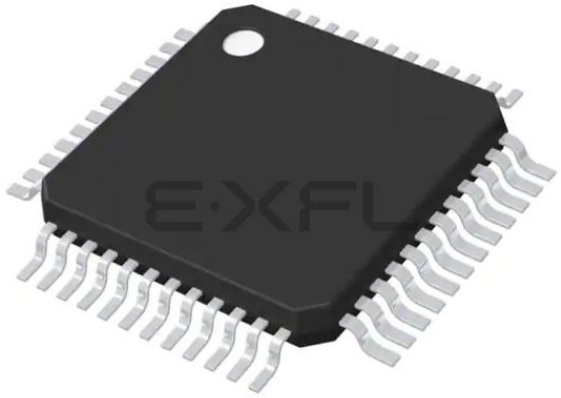
Infineon Technologies - SAK-XC886CM-6FFI 5V AC Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	XC800
Core Size	8-Bit
Speed	24MHz
Connectivity	CANbus, SSI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	34
Program Memory Size	24KB (24K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1.75K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	PG-TQFP-48
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/sak-xc886cm-6ffi-5v-ac

Table 3 Pin Definitions and Functions (cont'd)

Symbol	Pin Number (TQFP-48/64)	Type	Reset State	Function
P1.6	8/10		PU	CCPOS1_1 CCU6 Hall Input 1 T12HR_0 CCU6 Timer 12 Hardware Run Input EXINT6_0 External Interrupt Input 6 RXDC0_2 MultiCAN Node 0 Receiver Input T21_1 Timer 21 Input
P1.7	9/11		PU	CCPOS2_1 CCU6 Hall Input 2 T13HR_0 CCU6 Timer 13 Hardware Run Input T2_1 Timer 2 Input TXDC0_2 MultiCAN Node 0 Transmitter Output P1.5 and P1.6 can be used as a software chip select output for the SSC.

3.2 Memory Organization

The XC886/888 CPU operates in the following five address spaces:

- 12 Kbytes of Boot ROM program memory
- 256 bytes of internal RAM data memory
- 1.5 Kbytes of XRAM memory
  (XRAM can be read/written as program memory or external data memory)
- A 128-byte Special Function Register area
- 24/32 Kbytes of Flash program memory (Flash devices); or
  24/32 Kbytes of ROM program memory, with additional 4 Kbytes of Flash
  (ROM devices)

Figure 7 illustrates the memory address spaces of the 32-Kbyte Flash devices. For the 24-Kbyte Flash devices, the shaded banks are not available.

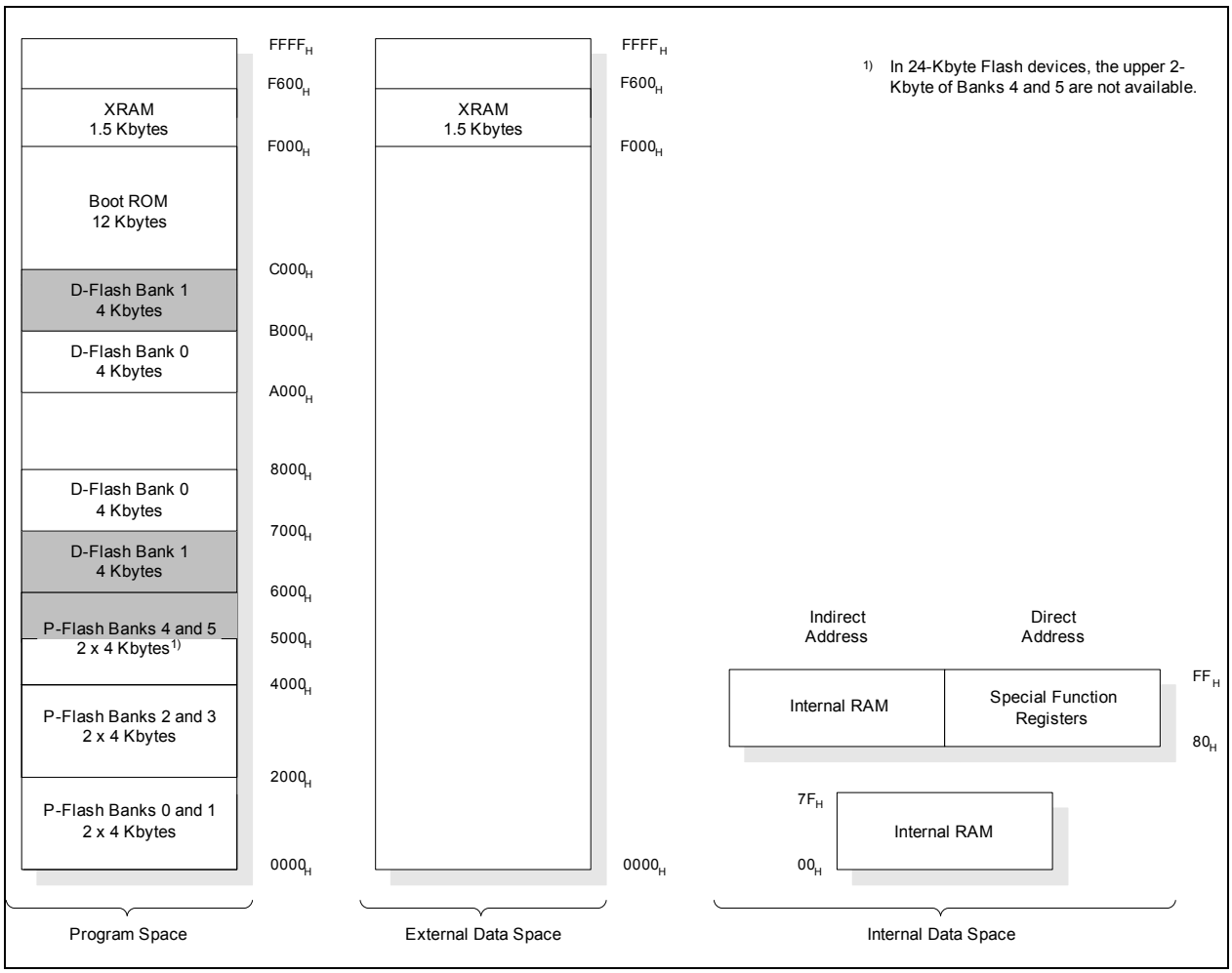

Figure 7 Memory Map of XC886/888 Flash Device

For both 24-Kbyte and 32-Kbyte ROM devices, the last four bytes of the ROM from $7FFC_H$ to $7FFF_H$ are reserved for the ROM signature and cannot be used to store user

SYSCON0
System Control Register 0 **Reset Value: 04_H**

7	6	5	4	3	2	1	0
	0		**IMODE**	**0**	**1**	**0**	**RMAP**
	r		rw	r	r	r	rw

Field	Bits	Type	Description
RMAP	0	rw	**Interrupt Node XINTR0 Enable** 0 The access to the standard SFR area is enabled 1 The access to the mapped SFR area is enabled
1	2	r	**Reserved** Returns 1 if read; should be written with 1.
0	[7:5], 3,1	r	**Reserved** Returns 0 if read; should be written with 0.

Note: The RMAP bit should be cleared/set by ANL or ORL instructions.

3.2.2.2 Address Extension by Paging

Address extension is further performed at the module level by paging. With the address extension by mapping, the XC886/888 has a 256-SFR address range. However, this is still less than the total number of SFRs needed by the on-chip peripherals. To meet this requirement, some peripherals have a built-in local address extension mechanism for increasing the number of addressable SFRs. The extended address range is not directly controlled by the CPU instruction itself, but is derived from bit field PAGE in the module page register MOD_PAGE. Hence, the bit field PAGE must be programmed before accessing the SFR of the target module. Each module may contain a different number of pages and a different number of SFRs per page, depending on the specific requirement. Besides setting the correct RMAP bit value to select the SFR area, the user must also ensure that a valid PAGE is selected to target the desired SFR. A page inside the extended address range can be selected as shown in **Figure 9**.

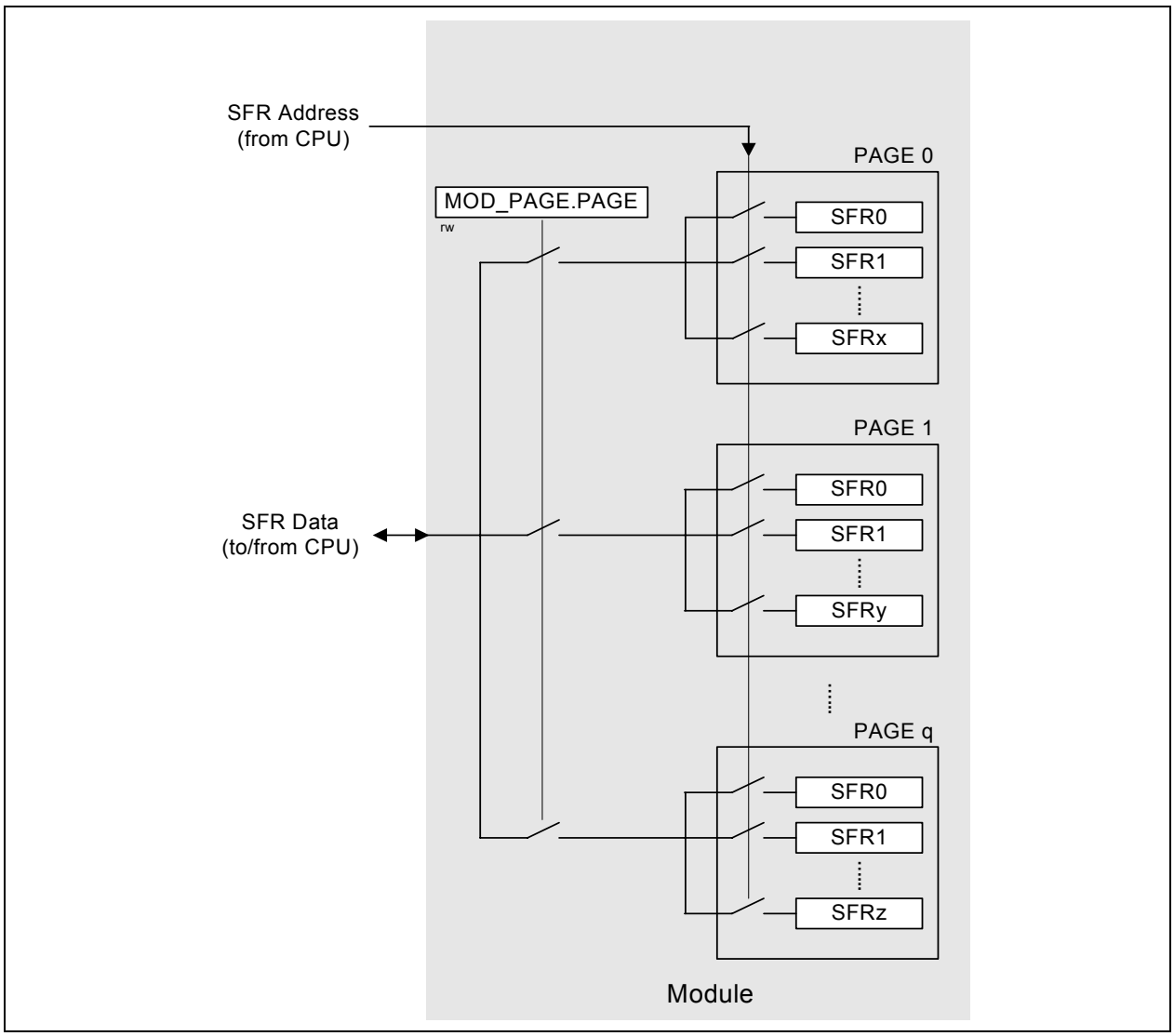

Figure 9 Address Extension by Paging

In order to access a register located in a page different from the actual one, the current page must be exited. This is done by reprogramming the bit field PAGE in the page register. Only then can the desired access be performed.

If an interrupt routine is initiated between the page register access and the module register access, and the interrupt needs to access a register located in another page, the current page setting can be saved, the new one programmed and the old page setting restored. This is possible with the storage fields STx (x = 0 - 3) for the save and restore action of the current page setting. By indicating which storage bit field should be used in parallel with the new page value, a single write operation can:

- Save the contents of PAGE in STx before overwriting with the new value
  (this is done in the beginning of the interrupt routine to save the current page setting and program the new page number); or

Table 5 CPU Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
$A8_H$	**IEN0** **Reset: 00_H** Interrupt Enable Register 0	Bit Field	EA	0	ET2	ES	ET1	EX1	ET0	EX0
		Type	rw	r	rw	rw	rw	rw	rw	rw
$B8_H$	**IP** **Reset: 00_H** Interrupt Priority Register	Bit Field	0		PT2	PS	PT1	PX1	PT0	PX0
		Type	r		rw	rw	rw	rw	rw	rw
$B9_H$	**IPH** **Reset: 00_H** Interrupt Priority High Register	Bit Field	0		PT2H	PSH	PT1H	PX1H	PT0H	PX0H
		Type	r		rw	rw	rw	rw	rw	rw
$D0_H$	**PSW** **Reset: 00_H** Program Status Word Register	Bit Field	CY	AC	F0	RS1	RS0	OV	F1	P
		Type	rwh	rwh	rw	rw	rw	rwh	rw	rh
$E0_H$	**ACC** **Reset: 00_H** Accumulator Register	Bit Field	ACC7	ACC6	ACC5	ACC4	ACC3	ACC2	ACC1	ACC0
		Type	rw	rw	rw	rw	rw	rw	rw	rw
$E8_H$	**IEN1** **Reset: 00_H** Interrupt Enable Register 1	Bit Field	ECCIP 3	ECCIP 2	ECCIP 1	ECCIP 0	EXM	EX2	ESSC	EADC
		Type	rw	rw	rw	rw	rw	rw	rw	rw
$F0_H$	**B** **Reset: 00_H** B Register	Bit Field	B7	B6	B5	B4	B3	B2	B1	B0
		Type	rw	rw	rw	rw	rw	rw	rw	rw
$F8_H$	**IP1** **Reset: 00_H** Interrupt Priority 1 Register	Bit Field	PCCIP 3	PCCIP 2	PCCIP 1	PCCIP 0	PXM	PX2	PSSC	PADC
		Type	rw	rw	rw	rw	rw	rw	rw	rw
$F9_H$	**IPH1** **Reset: 00_H** Interrupt Priority 1 High Register	Bit Field	PCCIP 3H	PCCIP 2H	PCCIP 1H	PCCIP 0H	PXMH	PX2H	PSSC H	PADC H
		Type	rw	rw	rw	rw	rw	rw	rw	rw

3.2.4.2 MDU Registers

The MDU SFRs can be accessed in the mapped memory area (RMAP = 1).

Table 6 MDU Register Overview

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
RMAP = 1										
$B0_H$	**MDUSTAT** **Reset: 00_H** MDU Status Register	Bit Field	0					BSY	IERR	IRDY
		Type	r					rh	rwh	rwh
$B1_H$	**MDUCON** **Reset: 00_H** MDU Control Register	Bit Field	IE	IR	RSEL	STAR T	OPCODE			
		Type	rw	rw	rw	rwh	rw			
$B2_H$	**MD0** **Reset: 00_H** MDU Operand Register 0	Bit Field	DATA							
		Type	rw							
$B2_H$	**MR0** **Reset: 00_H** MDU Result Register 0	Bit Field	DATA							
		Type	rh							
$B3_H$	**MD1** **Reset: 00_H** MDU Operand Register 1	Bit Field	DATA							
		Type	rw							

Table 8 SCU Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
BC_H	**NMISR** **Reset: 00_H** NMI Status Register	Bit Field	0	FNMI ECC	FNMI VDDP	FNMI VDD	FNMI OCDS	FNMI FLASH	FNMI PLL	FNMI WDT
		Type	r	rwh	rwh	rwh	rwh	rwh	rwh	rwh
BD_H	**BCON** **Reset: 00_H** Baud Rate Control Register	Bit Field	BGSEL		0	BRDIS	BRPRE			R
		Type	rw		r	rw	rw			rw
BE_H	**BG** **Reset: 00_H** Baud Rate Timer/Reload Register	Bit Field	BR_VALUE							
		Type	rwh							
$E9_H$	**FDCON** **Reset: 00_H** Fractional Divider Control Register	Bit Field	BGS	SYNE N	ERRS YN	EOFS YN	BRK	NDOV	FDM	FDEN
		Type	rw	rw	rwh	rwh	rwh	rwh	rw	rw
EA_H	**FDSTEP** **Reset: 00_H** Fractional Divider Reload Register	Bit Field	STEP							
		Type	rw							
EB_H	**FDRES** **Reset: 00_H** Fractional Divider Result Register	Bit Field	RESULT							
		Type	rh							
RMAP = 0, PAGE 1										
$B3_H$	**ID** **Reset: UU_H** Identity Register	Bit Field	PRODID					VERID		
		Type	r					r		
$B4_H$	**PMCON0** **Reset: 00_H** Power Mode Control Register 0	Bit Field	0	WDT RST	WKRS	WK SEL	SD	PD	WS	
		Type	r	rwh	rwh	rw	rw	rwh	rw	
$B5_H$	**PMCON1** **Reset: 00_H** Power Mode Control Register 1	Bit Field	0	CDC_ DIS	CAN_ DIS	MDU_ DIS	T2_ DIS	CCU_ DIS	SSC_ DIS	ADC_ DIS
		Type	r	rw	rw	rw	rw	rw	rw	rw
$B6_H$	**OSC_CON** **Reset: 08_H** OSC Control Register	Bit Field	0			OSC PD	XPD	OSC SS	ORD RES	OSCR
		Type	r			rw	rw	rw	rwh	rh
$B7_H$	**PLL_CON** **Reset: 90_H** PLL Control Register	Bit Field	NDIV				VCO BYP	OSC DISC	RESL D	LOCK
		Type	rw				rw	rw	rwh	rh
BA_H	**CMCON** **Reset: 10_H** Clock Control Register	Bit Field	VCO SEL	KDIV	0	FCCF G	CLKREL			
		Type	rw	rw	r	rw	rw			
BB_H	**PASSWD** **Reset: 07_H** Password Register	Bit Field	PASS					PROT ECT_S	MODE	
		Type	wh					rh	rw	
BC_H	**FEAL** **Reset: 00_H** Flash Error Address Register Low	Bit Field	ECCERRADDR							
		Type	rh							
BD_H	**FEAH** **Reset: 00_H** Flash Error Address Register High	Bit Field	ECCERRADDR							
		Type	rh							

Table 11 ADC Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
CC_H	**ADC_CHINSR Reset: 00_H** Channel Interrupt Set Register	Bit Field	CHINS 7	CHINS 6	CHINS 5	CHINS 4	CHINS 3	CHINS 2	CHINS 1	CHINS 0
		Type	w	w	w	w	w	w	w	w
CD_H	**ADC_CHINPR Reset: 00_H** Channel Interrupt Node Pointer Register	Bit Field	CHINP 7	CHINP 6	CHINP 5	CHINP 4	CHINP 3	CHINP 2	CHINP 1	CHINP 0
		Type	rw	rw	rw	rw	rw	rw	rw	rw
CE_H	**ADC_EVINFR Reset: 00_H** Event Interrupt Flag Register	Bit Field	EVINF 7	EVINF 6	EVINF 5	EVINF 4	0		EVINF 1	EVINF 0
		Type	rh	rh	rh	rh	r		rh	rh
CF_H	**ADC_EVINCR Reset: 00_H** Event Interrupt Clear Flag Register	Bit Field	EVINC 7	EVINC 6	EVINC 5	EVINC 4	0		EVINC 1	EVINC 0
		Type	w	w	w	w	r		w	w
$D2_H$	**ADC_EVINSR Reset: 00_H** Event Interrupt Set Flag Register	Bit Field	EVINS 7	EVINS 6	EVINS 5	EVINS 4	0		EVINS 1	EVINS 0
		Type	w	w	w	w	r		w	w
$D3_H$	**ADC_EVINPR Reset: 00_H** Event Interrupt Node Pointer Register	Bit Field	EVINP 7	EVINP 6	EVINP 5	EVINP 4	0		EVINP 1	EVINP 0
		Type	rw	rw	rw	rw	r		rw	rw
RMAP = 0, PAGE 6										
CA_H	**ADC_CRCR1 Reset: 00_H** Conversion Request Control Register 1	Bit Field	CH7	CH6	CH5	CH4	0			
		Type	rwh	rwh	rwh	rwh	r			
CB_H	**ADC_CRPR1 Reset: 00_H** Conversion Request Pending Register 1	Bit Field	CHP7	CHP6	CHP5	CHP4	0			
		Type	rwh	rwh	rwh	rwh	r			
CC_H	**ADC_CRMR1 Reset: 00_H** Conversion Request Mode Register 1	Bit Field	Rsv	LDEV	CLRP ND	SCAN	ENSI	ENTR	0	ENGT
		Type	r	w	w	rw	rw	rw	r	rw
CD_H	**ADC_QMR0 Reset: 00_H** Queue Mode Register 0	Bit Field	CEV	TREV	FLUS H	CLRV	0	ENTR	0	ENGT
		Type	w	w	w	w	r	rw	r	rw
CE_H	**ADC_QSR0 Reset: 20_H** Queue Status Register 0	Bit Field	Rsv	0	EMPT Y	EV	0		FILL	
		Type	r	r	rh	rh	r		rh	
CF_H	**ADC_Q0R0 Reset: 00_H** Queue 0 Register 0	Bit Field	EXTR	ENSI	RF	V	0	REQCHNR		
		Type	rh	rh	rh	rh	r	rh		
$D2_H$	**ADC_QBUR0 Reset: 00_H** Queue Backup Register 0	Bit Field	EXTR	ENSI	RF	V	0	REQCHNR		
		Type	rh	rh	rh	rh	r	rh		
$D2_H$	**ADC_QINR0 Reset: 00_H** Queue Input Register 0	Bit Field	EXTR	ENSI	RF	0		REQCHNR		
		Type	w	w	w	r		w		

Table 14 CCU6 Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
FA_H	**CCU6_CC60SRL Reset: 00_H** Capture/Compare Shadow Register for Channel CC60 Low	Bit Field	CC60SL							
		Type	rwh							
FB_H	**CCU6_CC60SRH Reset: 00_H** Capture/Compare Shadow Register for Channel CC60 High	Bit Field	CC60SH							
		Type	rwh							
FC_H	**CCU6_CC61SRL Reset: 00_H** Capture/Compare Shadow Register for Channel CC61 Low	Bit Field	CC61SL							
		Type	rwh							
FD_H	**CCU6_CC61SRH Reset: 00_H** Capture/Compare Shadow Register for Channel CC61 High	Bit Field	CC61SH							
		Type	rwh							
FE_H	**CCU6_CC62SRL Reset: 00_H** Capture/Compare Shadow Register for Channel CC62 Low	Bit Field	CC62SL							
		Type	rwh							
FF_H	**CCU6_CC62SRH Reset: 00_H** Capture/Compare Shadow Register for Channel CC62 High	Bit Field	CC62SH							
		Type	rwh							
RMAP = 0, PAGE 1										
$9A_H$	**CCU6_CC63RL Reset: 00_H** Capture/Compare Register for Channel CC63 Low	Bit Field	CC63VL							
		Type	rh							
$9B_H$	**CCU6_CC63RH Reset: 00_H** Capture/Compare Register for Channel CC63 High	Bit Field	CC63VH							
		Type	rh							
$9C_H$	**CCU6_T12PRL Reset: 00_H** Timer T12 Period Register Low	Bit Field	T12PVL							
		Type	rwh							
$9D_H$	**CCU6_T12PRH Reset: 00_H** Timer T12 Period Register High	Bit Field	T12PVH							
		Type	rwh							
$9E_H$	**CCU6_T13PRL Reset: 00_H** Timer T13 Period Register Low	Bit Field	T13PVL							
		Type	rwh							
$9F_H$	**CCU6_T13PRH Reset: 00_H** Timer T13 Period Register High	Bit Field	T13PVH							
		Type	rwh							
$A4_H$	**CCU6_T12DTCL Reset: 00_H** Dead-Time Control Register for Timer T12 Low	Bit Field	DTM							
		Type	rw							
$A5_H$	**CCU6_T12DTCH Reset: 00_H** Dead-Time Control Register for Timer T12 High	Bit Field	0	DTR2	DTR1	DTR0	0	DTE2	DTE1	DTE0
		Type	r	rh	rh	rh	r	rw	rw	rw
$A6_H$	**CCU6_TCTR0L Reset: 00_H** Timer Control Register 0 Low	Bit Field	CTM	CDIR	STE12	T12R	T12PRE	T12CLK		
		Type	rw	rh	rh	rh	rw	rw		
$A7_H$	**CCU6_TCTR0H Reset: 00_H** Timer Control Register 0 High	Bit Field	0		STE13	T13R	T13PRE	T13CLK		
		Type	r		rh	rh	rw	rw		
FA_H	**CCU6_CC60RL Reset: 00_H** Capture/Compare Register for Channel CC60 Low	Bit Field	CC60VL							
		Type	rh							

Table 14 CCU6 Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
FB_H	**CCU6_TCTR2H Reset: 00_H** Timer Control Register 2 High	Bit Field	0				T13RSEL		T12RSEL	
		Type	r				rw		rw	
FC_H	**CCU6_MODCTRL Reset: 00_H** Modulation Control Register Low	Bit Field	MCM EN	0	T12MODEN					
		Type	rw	r	rw					
FD_H	**CCU6_MODCTRH Reset: 00_H** Modulation Control Register High	Bit Field	ECT13O	0	T13MODEN					
		Type	rw	r	rw					
FE_H	**CCU6_TRPCTRL Reset: 00_H** Trap Control Register Low	Bit Field	0					TRPM2	TRPM1	TRPM0
		Type	r					rw	rw	rw
FF_H	**CCU6_TRPCTRH Reset: 00_H** Trap Control Register High	Bit Field	TRPPEN	TRPEN13	TRPEN					
		Type	rw	rw	rw					
RMAP = 0, PAGE 3										
$9A_H$	**CCU6_MCMOUTL Reset: 00_H** Multi-Channel Mode Output Register Low	Bit Field	0	R	MCMP					
		Type	r	rh	rh					
$9B_H$	**CCU6_MCMOUTH Reset: 00_H** Multi-Channel Mode Output Register High	Bit Field	0		CURH			EXPH		
		Type	r		rh			rh		
$9C_H$	**CCU6_ISL Reset: 00_H** Capture/Compare Interrupt Status Register Low	Bit Field	T12PM	T12OM	ICC62F	ICC62R	ICC61F	ICC61R	ICC60F	ICC60R
		Type	rh	rh	rh	rh	rh	rh	rh	rh
$9D_H$	**CCU6_ISH Reset: 00_H** Capture/Compare Interrupt Status Register High	Bit Field	STR	IDLE	WHE	CHE	TRPS	TRPF	T13PM	T13CM
		Type	rh	rh	rh	rh	rh	rh	rh	rh
$9E_H$	**CCU6_PISEL0L Reset: 00_H** Port Input Select Register 0 Low	Bit Field	ISTRP		ISCC62		ISCC61		ISCC60	
		Type	rw		rw		rw		rw	
$9F_H$	**CCU6_PISEL0H Reset: 00_H** Port Input Select Register 0 High	Bit Field	IST12HR		ISPOS2		ISPOS1		ISPOS0	
		Type	rw		rw		rw		rw	
$A4_H$	**CCU6_PISEL2 Reset: 00_H** Port Input Select Register 2	Bit Field	0						IST13HR	
		Type	r						rw	
FA_H	**CCU6_T12L Reset: 00_H** Timer T12 Counter Register Low	Bit Field	T12CVL							
		Type	rwh							
FB_H	**CCU6_T12H Reset: 00_H** Timer T12 Counter Register High	Bit Field	T12CVH							
		Type	rwh							
FC_H	**CCU6_T13L Reset: 00_H** Timer T13 Counter Register Low	Bit Field	T13CVL							
		Type	rwh							
FD_H	**CCU6_T13H Reset: 00_H** Timer T13 Counter Register High	Bit Field	T13CVH							
		Type	rwh							

Table 18 OCDS Register Overview (cont'd)

Addr	Register Name	Bit	7	6	5	4	3	2	1	0
EC_H	**MMWR2** **Reset: 00_H** Monitor Work Register 2	Bit Field	MMWR2							
		Type	rw							

3.3 Flash Memory

The Flash memory provides an embedded user-programmable non-volatile memory, allowing fast and reliable storage of user code and data. It is operated from a single 2.5 V supply from the Embedded Voltage Regulator (EVR) and does not require additional programming or erasing voltage. The sectorization of the Flash memory allows each sector to be erased independently.

Features

- In-System Programming (ISP) via UART
- In-Application Programming (IAP)
- Error Correction Code (ECC) for dynamic correction of single-bit errors
- Background program and erase operations for CPU load minimization
- Support for aborting erase operation
- Minimum program width[1] of 32-byte for D-Flash and 64-byte for P-Flash
- 1-sector minimum erase width
- 1-byte read access
- Flash is delivered in erased state (read all zeros)
- Operating supply voltage: 2.5 V ± 7.5 %
- Read access time: 3 × t_{CCLK} = 125 ns[2]
- Program time: 248256 / f_{SYS} = 2.6 ms[3]
- Erase time: 9807360 / f_{SYS} = 102 ms[3]

1) P-Flash: 64-byte wordline can only be programmed once, i.e., one gate disturb allowed.
D-Flash: 32-byte wordline can be programmed twice, i.e., two gate disturbs allowed.

2) Values shown here are typical values. f_{sys} = 96 MHz ± 7.5% (f_{CCLK} = 24 MHz ± 7.5 %) is the maximum frequency range for Flash read access.

3) Values shown here are typical values. f_{sys} = 96 MHz ± 7.5% is the only frequency range for Flash programming and erasing. f_{sysmin} is used for obtaining the worst case timing.

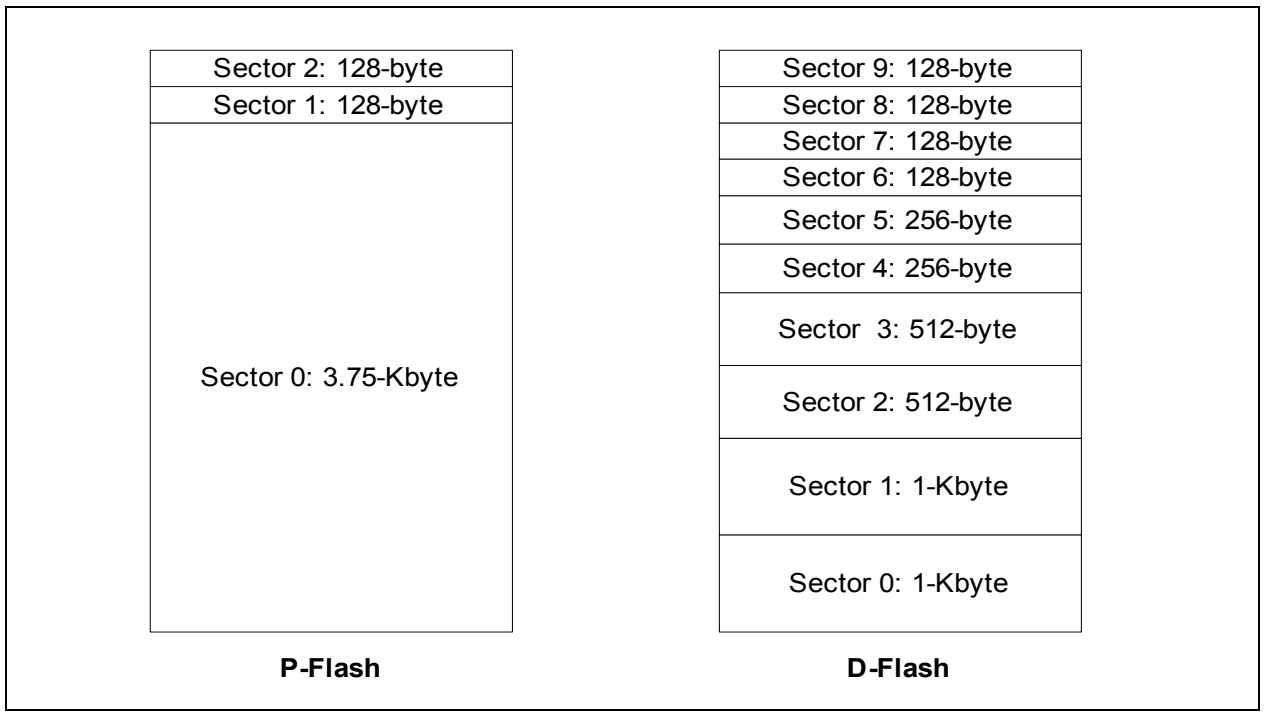

Figure 11 Flash Bank Sectorization

The internal structure of each Flash bank represents a sector architecture for flexible erase capability. The minimum erase width is always a complete sector, and sectors can be erased separately or in parallel. Contrary to standard EPROMs, erased Flash memory cells contain 0s.

The D-Flash bank is divided into more physical sectors for extended erasing and reprogramming capability; even numbers for each sector size are provided to allow greater flexibility and the ability to adapt to a wide range of application requirements.

3.3.2 Parallel Read Access of P-Flash

To enhance system performance, the P-Flash banks are configured for parallel read to allow two bytes of linear code to be read in 4 x CCLK cycles, compared to 6 x CCLK cycles if serial read is performed. This is achieved by reading two bytes in parallel from a P-Flash bank pair within the 3 x CCLK cycles access time and storing them in a cache. Subsequent read from the cache by the CPU does not require a wait state and can be completed within 1 x CCLK cycle. The result is the average instruction fetch time from the P-Flash banks is reduced and thus, the MIPS (Mega Instruction Per Second) of the system is increased.

However, if the parallel read feature is not desired due to certain timing constraints, it can be disabled by calling the parallel read disable subroutine.

3.3.3 Flash Programming Width

For the P-Flash banks, a programmed wordline (WL) must be erased before it can be reprogrammed as the Flash cells can only withstand one gate disturb. This means that the entire sector containing the WL must be erased since it is impossible to erase a single WL.

For the D-Flash bank, the same WL can be programmed twice before erasing is required as the Flash cells are able to withstand two gate disturbs. This means if the number of data bytes that needs to be written is smaller than the 32-byte minimum programming width, the user can opt to program this number of data bytes (x; where x can be any integer from 1 to 31) first and program the remaining bytes (32 - x) later. Hence, it is possible to program the same WL, for example, with 16 bytes of data two times (see **Figure 12**)

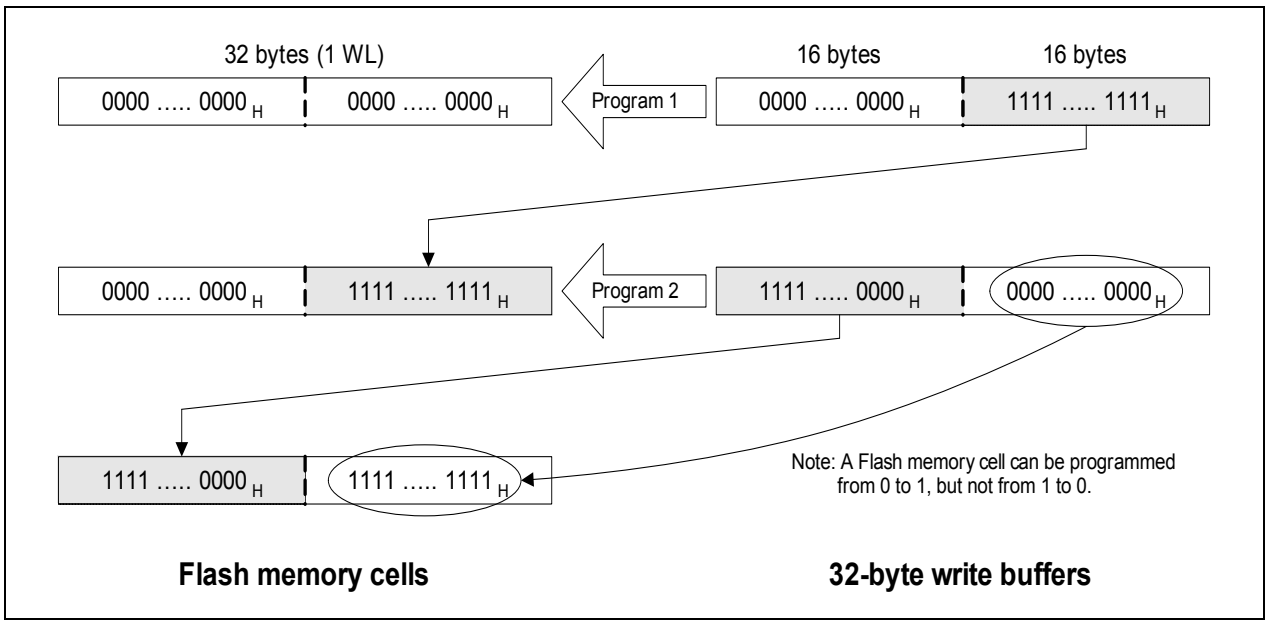

Figure 12 D-Flash Programming

Note: When programming a D-Flash WL the second time, the previously programmed Flash memory cells (whether 0s or 1s) should be reprogrammed with 0s to retain its original contents and to prevent "over-programming".

3.4 Interrupt System

The XC800 Core supports one non-maskable interrupt (NMI) and 14 maskable interrupt requests. In addition to the standard interrupt functions supported by the core, e.g., configurable interrupt priority and interrupt masking, the XC886/888 interrupt system provides extended interrupt support capabilities such as the mapping of each interrupt vector to several interrupt sources to increase the number of interrupt sources supported, and additional status registers for detecting and determining the interrupt source.

3.4.1 Interrupt Source

Figure 13 to **Figure 17** give a general overview of the interrupt sources and nodes, and their corresponding control and status flags.

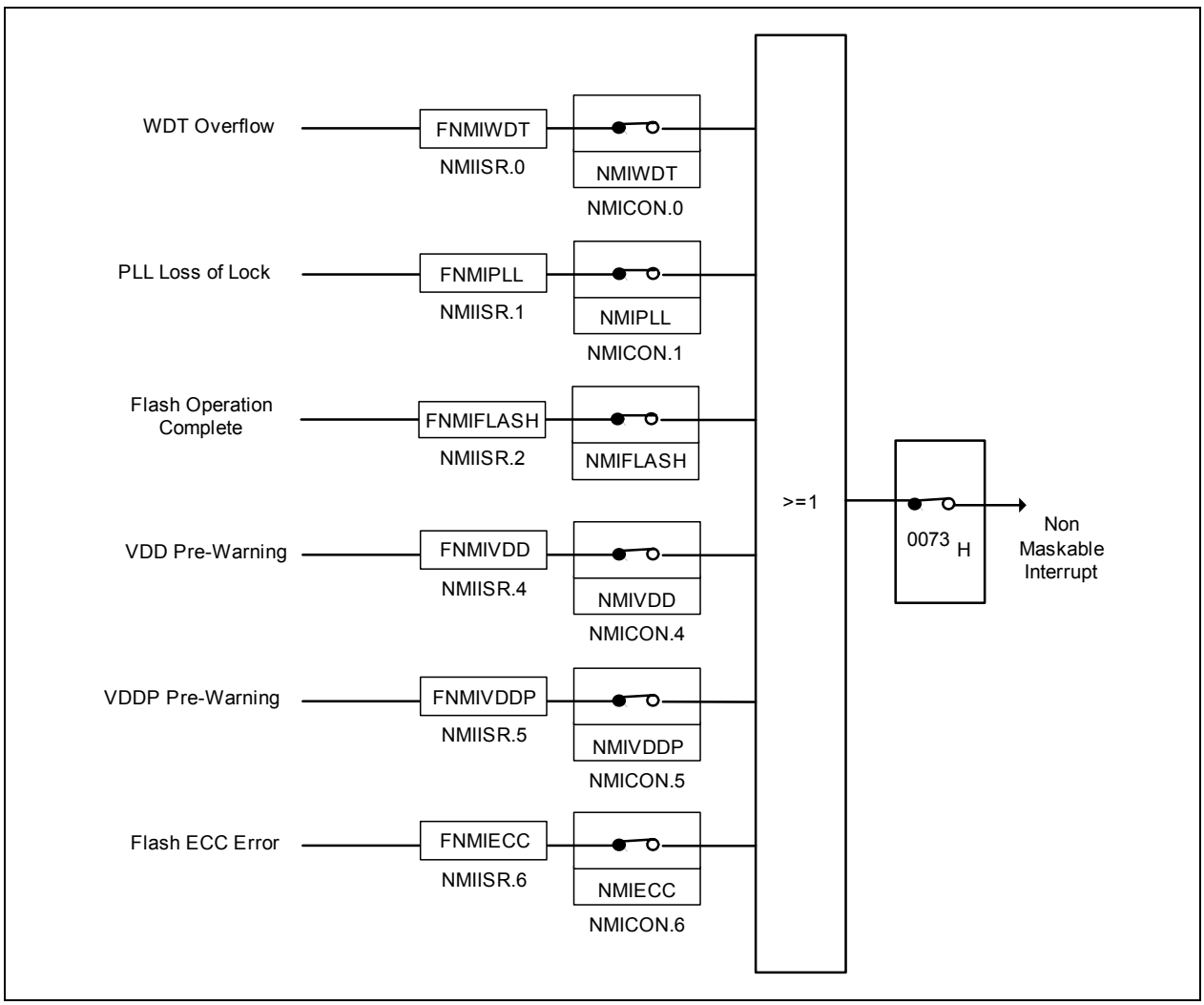

Figure 13 Non-Maskable Interrupt Request Sources

For power saving purposes, the clocks may be disabled or slowed down according to Table 26.

Table 26 System frequency (f_{sys} = 96 MHz)

Power Saving Mode	Action
Idle	Clock to the CPU is disabled.
Slow-down	Clocks to the CPU and all the peripherals are divided by a common programmable factor defined by bit field CMCON.CLKREL.
Power-down	Oscillator and PLL are switched off.

3.9 Power Saving Modes

The power saving modes of the XC886/888 provide flexible power consumption through a combination of techniques, including:

- Stopping the CPU clock
- Stopping the clocks of individual system components
- Reducing clock speed of some peripheral components
- Power-down of the entire system with fast restart capability

After a reset, the active mode (normal operating mode) is selected by default (see **Figure 27**) and the system runs in the main system clock frequency. From active mode, different power saving modes can be selected by software. They are:

- Idle mode
- Slow-down mode
- Power-down mode

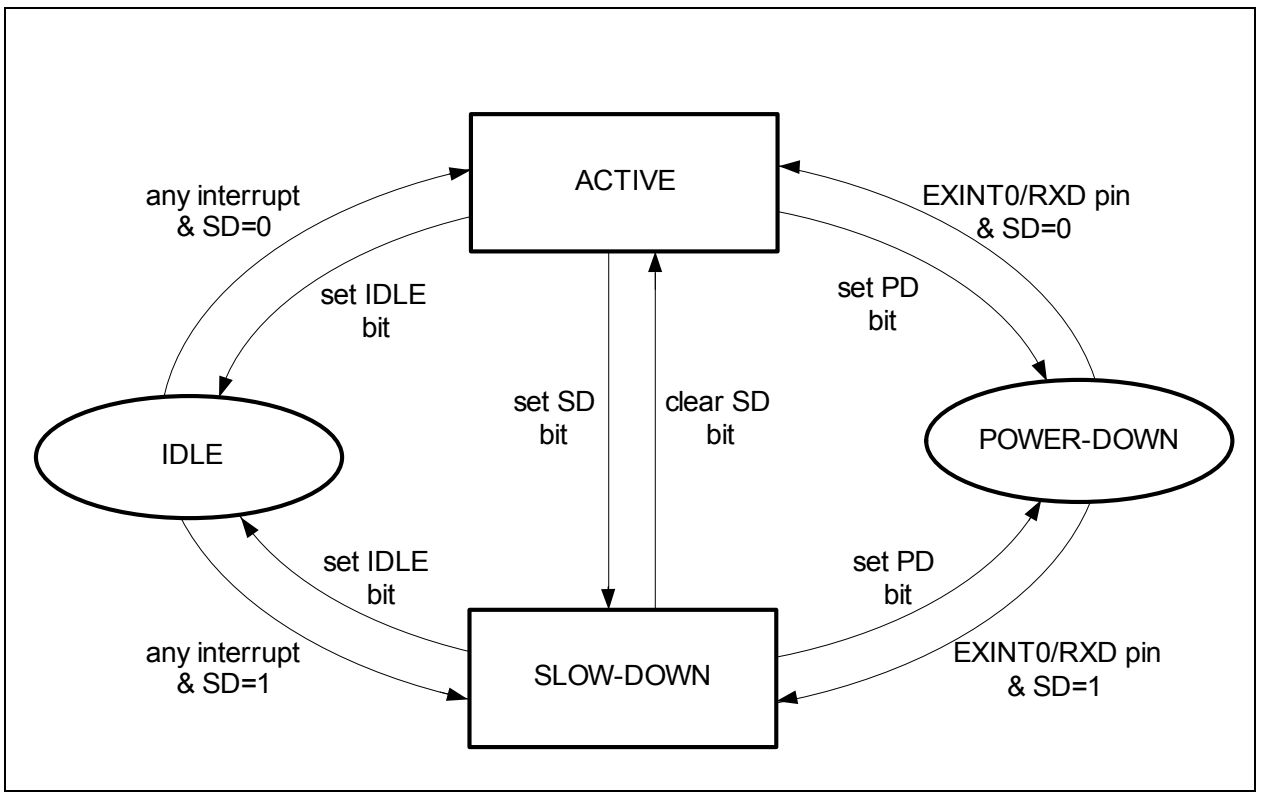

Figure 27 Transition between Power Saving Modes

4.1.2 Absolute Maximum Rating

Maximum ratings are the extreme limits to which the XC886/888 can be subjected to without permanent damage.

Table 4-1 Absolute Maximum Rating Parameters

Parameter	Symbol	Limit Values		Unit	Notes
		min.	max.		
Ambient temperature	T_A	-40	125	°C	under bias
Storage temperature	T_{ST}	-65	150	°C	1)
Junction temperature	T_J	-40	150	°C	under bias1)
Voltage on power supply pin with respect to V_{SS}	V_{DDP}	-0.5	6	V	1)
Voltage on any pin with respect to V_{SS}	V_{IN}	-0.5	V_{DDP} + 0.5 or max. 6	V	whichever is lower1)
Input current on any pin during overload condition	I_{IN}	-10	10	mA	1)
Absolute sum of all input currents during overload condition	$\Sigma\|I_{IN}\|$	–	50	mA	1)

1) Not subjected to production test, verified by design/characterization.

Note: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. During absolute maximum rating overload conditions ($V_{IN} > V_{DDP}$ or $V_{IN} < V_{SS}$) the voltage on V_{DDP} pin with respect to ground (V_{SS}) must not exceed the values defined by the absolute maximum ratings.

Table 40 ADC Characteristics (Operating Conditions apply; V_{DDP} = 5V Range)

Parameter	Symbol		Limit Values			Unit	Test Conditions/ Remarks
			min.	typ .	max.		
Overload current coupling factor for digital I/O pins	K_{OVD}	CC	–	–	5.0 x 10^{-3}	–	$I_{OV} > 0$ 1)3)
			–	–	1.0 x 10^{-2}	–	$I_{OV} < 0$ 1)3)
Switched capacitance at the reference voltage input	C_{AREFSW}	CC	–	10	20	pF	1)4)
Switched capacitance at the analog voltage inputs	C_{AINSW}	CC	–	5	7	pF	1)5)
Input resistance of the reference input	R_{AREF}	CC	–	1	2	kΩ	1)
Input resistance of the selected analog channel	R_{AIN}	CC	–	1	1.5	kΩ	1)

1) Not subjected to production test, verified by design/characterization

2) TUE is tested at V_{AREF} = 5.0 V, V_{AGND} = 0 V, V_{DDP} = 5.0 V.

3) An overload current (I_{OV}) through a pin injects a certain error current (I_{INJ}) into the adjacent pins. This error current adds to the respective pin's leakage current (I_{OZ}). The amount of error current depends on the overload current and is defined by the overload coupling factor K_{OV}. The polarity of the injected error current is inverse compared to the polarity of the overload current that produces it. The total current through a pin is $|I_{TOT}| = |I_{OZ1}| + (|I_{OV}| \times K_{OV})$. The additional error current may distort the input voltage on analog inputs.

4) This represents an equivalent switched capacitance. This capacitance is not switched to the reference voltage at once. Instead of this, smaller capacitances are successively switched to the reference voltage.

5) The sampling capacity of the conversion C-Network is pre-charged to $V_{AREF}/2$ before connecting the input to the C-Network. Because of the parasitic elements, the voltage measured at ANx is lower than $V_{AREF}/2$.

Table 42 Power Down Current (Operating Conditions apply; V_{DDP} = 5V range)

Parameter	Symbol	Limit Values		Unit	Test Condition
		typ.[1]	max.[2]		
V_{DDP} = 5V Range					
Power-Down Mode	I_{PDP}	1	10	µA	T_A = + 25 °C[3][4]
		-	30	µA	T_A = + 85 °C[4][5]

1) The typical I_{PDP} values are measured at V_{DDP} = 5.0 V.

2) The maximum I_{PDP} values are measured at V_{DDP} = 5.5 V.

3) I_{PDP} has a maximum value of 200 µA at T_A = + 125 °C.

4) I_{PDP} is measured with: $\overline{\text{RESET}}$ = V_{DDP}, V_{AGND}= V_{SS}, RXD/INT0 = V_{DDP}; rest of the ports are programmed to be input with either internal pull devices enabled or driven externally to ensure no floating inputs.

5) Not subjected to production test, verified by design/characterization.

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